

# High Voltage Power MOSFET

## IXTJ3N150

(Electrically Isolated Tab)

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



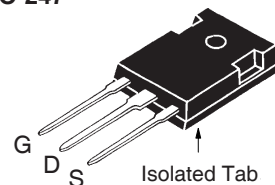
$$V_{DSS} = 1500V$$

$$I_{D25} = 2.3A$$

$$R_{DS(on)} \leq 8.0\Omega$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	2.3	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	9.0	A
$I_A$	$T_C = 25^\circ C$	3	A
$E_{AS}$	$T_C = 25^\circ C$	250	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	5	V/ns
$P_D$	$T_C = 25^\circ C$	110	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Torque	1.13 / 10	Nm/lb.in
$V_{ISOL}$	50/60 Hz, RM, t = 1min	2500	V~
<b>Weight</b>		5	g

ISO TO-247™



G = Gate      D = Drain  
S = Source

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Fast Intrinsic Diode
- Avalanche Rated
- Molding Epoxies meet UL 94 V-0 Flammability Classification

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

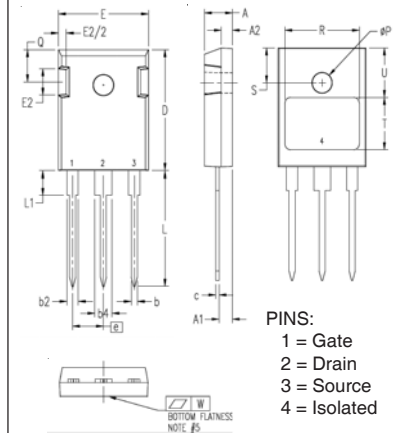
### Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	1500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			10 $\mu A$ 100 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 1.5A$ , Note 1			8.0 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 1.5\text{A}$ , Note 1	2.2	3.6	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1375	pF
$C_{oss}$			90	pF
$C_{rss}$			30	pF
$R_{GI}$	Gate Input Resistance		3.0	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 1.5\text{A}$ $R_G = 5\Omega$ (External)		19	ns
$t_r$			21	ns
$t_{d(off)}$			42	ns
$t_f$			25	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 1.5\text{A}$		38.6	nC
$Q_{gs}$			6.5	nC
$Q_{gd}$			19.0	nC
$R_{thJC}$			1.13	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### ISO TO-247 (IXTJ) OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.087	.100	2.21	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.085	1.91	2.16
b4	.115	.126	2.92	3.20
c	.023	.033	0.58	0.84
D	.820	.840	20.83	21.34
E	.620	.635	15.75	16.13
E2	.175	.195	4.44	4.95
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.160	.177	4.06	4.50
Q	.220	.240	5.59	6.10
R	.520	.540	13.21	13.72
S	.242 BSC		6.15 BSC	
T	.355	.375	9.02	9.53
U	.345	.370	8.76	9.40
$\phi P$	.140	.144	3.55	3.66
W	.000	.004	0.00	0.10

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$ , Note 1			3 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			12 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 1.5\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		0.9	$\mu\text{s}$
$Q_{RM}$			6.7	$\mu\text{C}$
$I_{RM}$			15.0	A

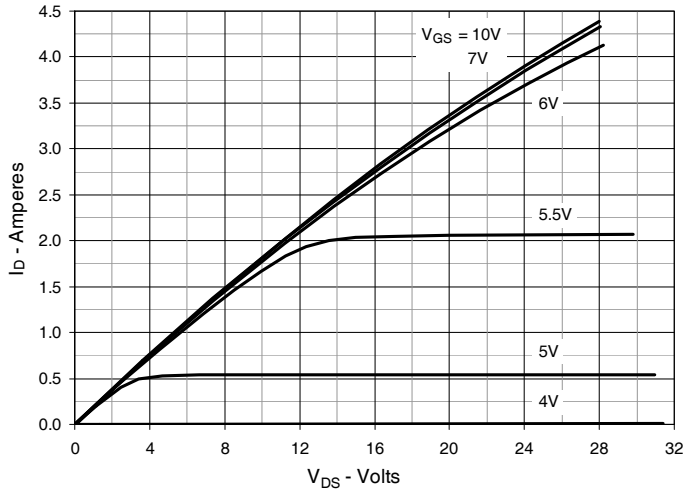
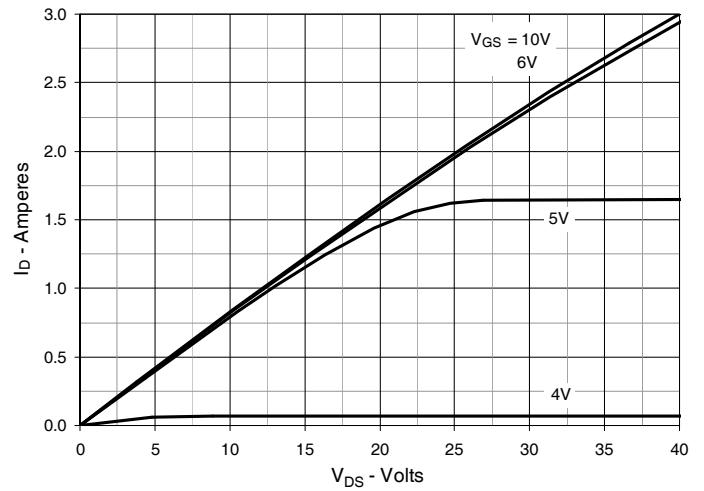
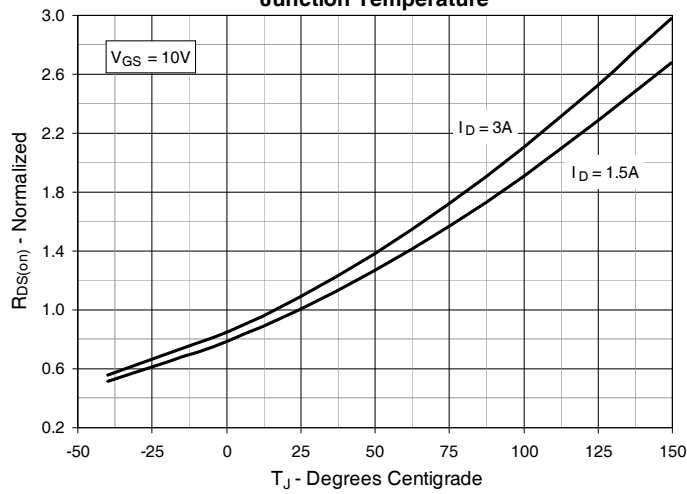
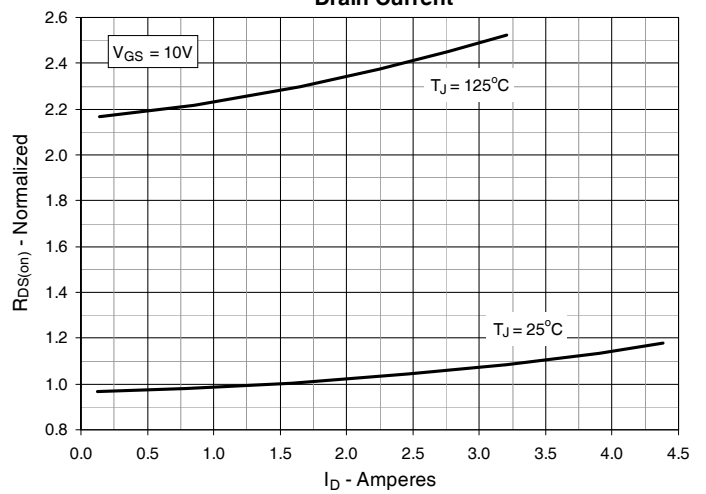
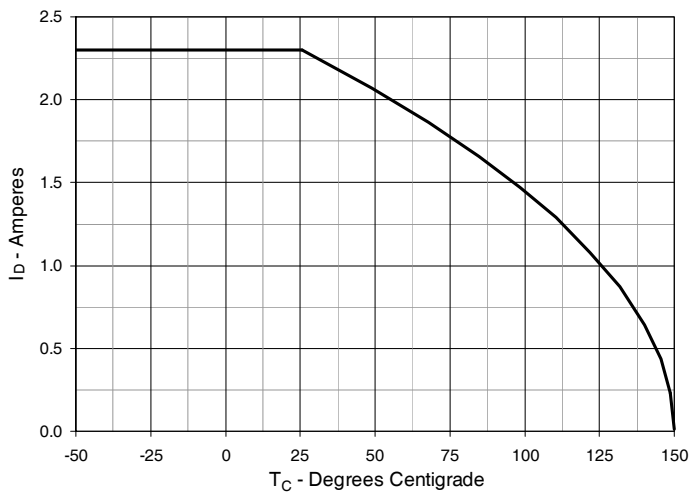
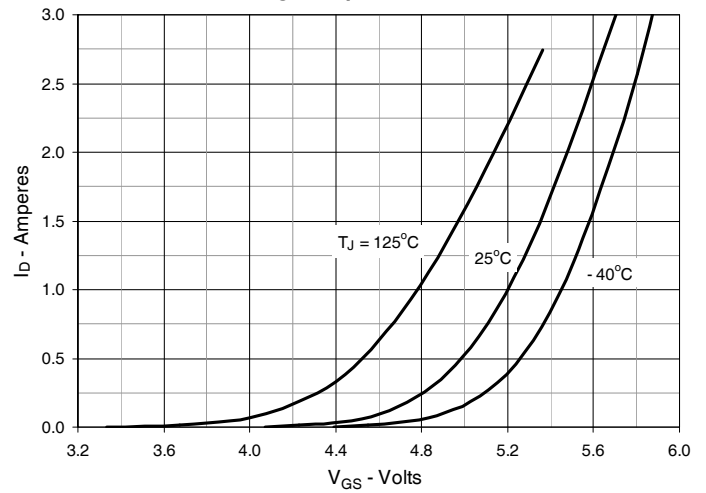
Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### ADVANCE TECHNICAL INFORMATION

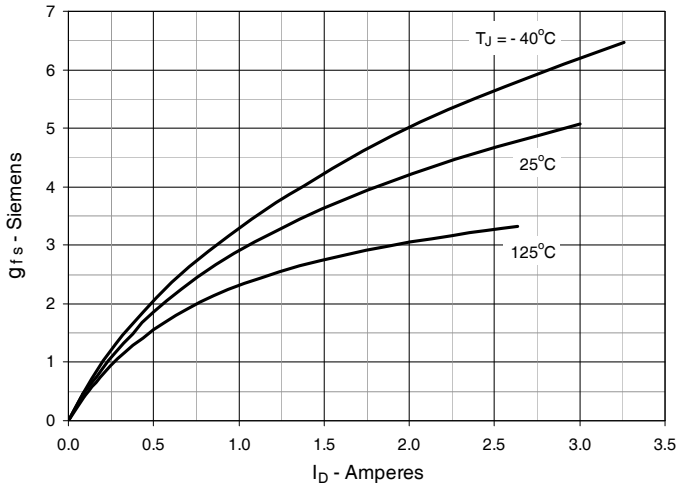
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

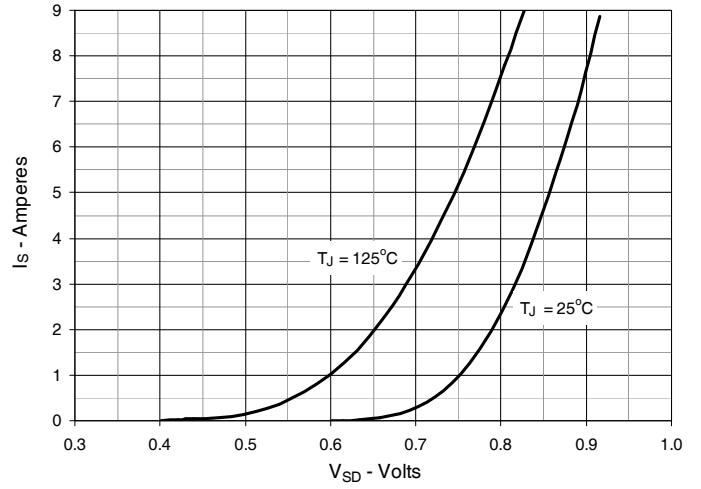
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 1.5\text{A}$  Value vs. Junction Temperature**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 1.5\text{A}$  Value vs. Drain Current**

**Fig. 5. Maximum Drain Current vs. Case Temperature**

**Fig. 6. Input Admittance**


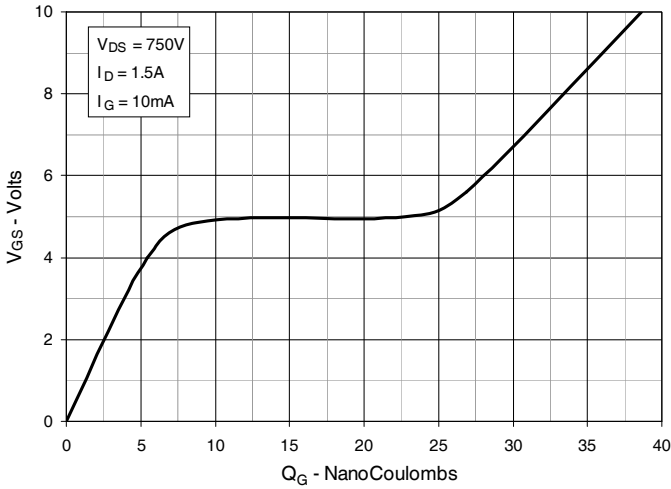
**Fig. 7. Transconductance**



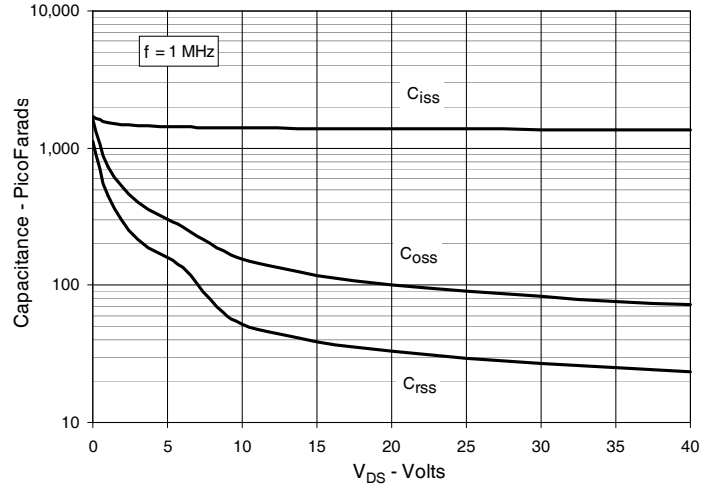
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



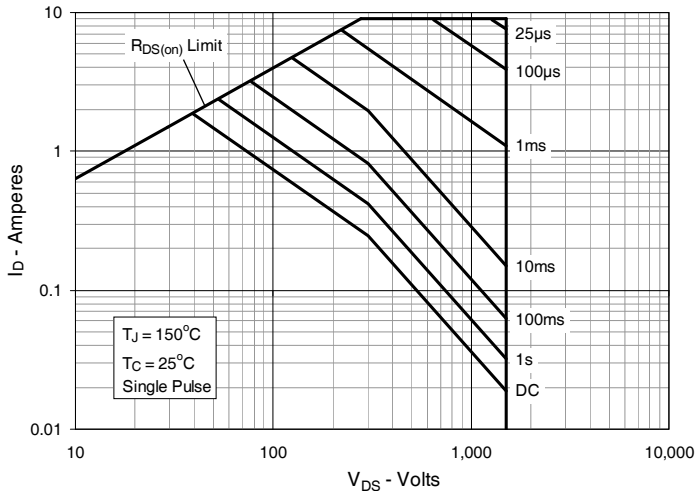
**Fig. 9. Gate Charge**



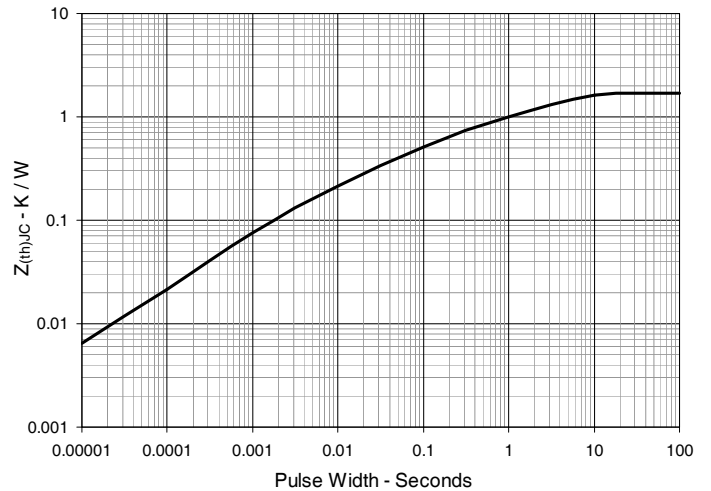
**Fig. 10. Capacitance**



**Fig. 11. Forward-Bias Safe Operating Area**



**Fig. 12. Maximum Transient Thermal Impedance**





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).